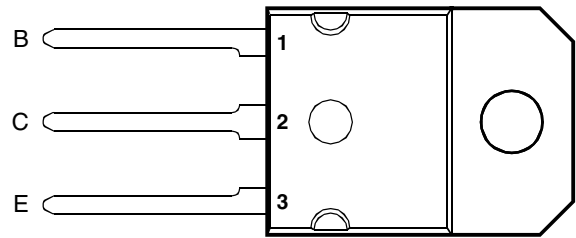


- Designed for Complementary Use with the BD546 Series
- 85 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Customer-Specified Selections Available

SOT-93 PACKAGE
(TOP VIEW)



MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BD545	V_{CBO}	40	V
	BD545A		60	
	BD545B		80	
	BD545C		100	
Collector-emitter voltage ($I_B = 0$) (see Note 1)	BD545	V_{CEO}	40	V
	BD545A		60	
	BD545B		80	
	BD545C		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	15	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	85	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Operating free air temperature range		T_A	-65 to +150	°C
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

- NOTES: 1. These values apply when the base-emitter diode is open circuited.
 2. Derate linearly to 150°C case temperature at the rate of 0.68 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 4)	$I_B = 0$	BD545	40			V
			BD545A	60			
			BD545B	80			
			BD545C	100			
I_{CES} Collector-emitter cut-off current	$V_{CE} = 40 \text{ V}$	$V_{BE} = 0$	BD545			0.4	mA
	$V_{CE} = 60 \text{ V}$	$V_{BE} = 0$	BD545A			0.4	
	$V_{CE} = 80 \text{ V}$	$V_{BE} = 0$	BD545B			0.4	
	$V_{CE} = 100 \text{ V}$	$V_{BE} = 0$	BD545C			0.4	
I_{CEO} Collector cut-off current	$V_{CE} = 30 \text{ V}$	$I_B = 0$	BD545/545A			0.7	mA
	$V_{CE} = 60 \text{ V}$	$I_B = 0$	BD545B/545C			0.7	
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$	$I_C = 1 \text{ A}$		60			
	$V_{CE} = 4 \text{ V}$	$I_C = 5 \text{ A}$	(see Notes 4 and 5)	25			
	$V_{CE} = 4 \text{ V}$	$I_C = 10 \text{ A}$		10			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 625 \text{ mA}$ $I_B = 2 \text{ A}$	$I_C = 5 \text{ A}$	(see Notes 4 and 5)			0.8	V
		$I_C = 10 \text{ A}$				1	
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$	$I_C = 10 \text{ A}$	(see Notes 4 and 5)			1.8	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.47	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			35.7	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = 6 \text{ A}$	$I_{B(on)} = 0.6 \text{ A}$	$I_{B(off)} = -0.6 \text{ A}$		0.6		μs
t_{off} Turn-off time				$V_{BE(off)} = -4 \text{ V}$	$R_L = 5 \Omega$	$t_p = 20 \mu\text{s}$, dc $\leq 2\%$	1

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

**TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT**

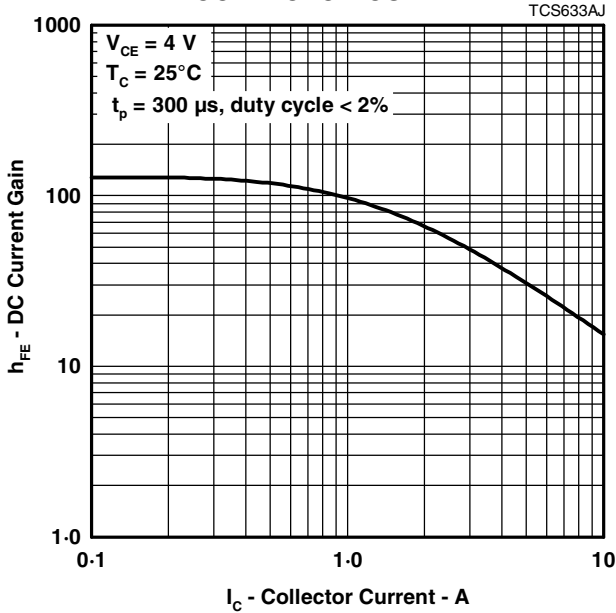


Figure 1.

**COLLECTOR-EMITTER SATURATION VOLTAGE
vs
BASE CURRENT**

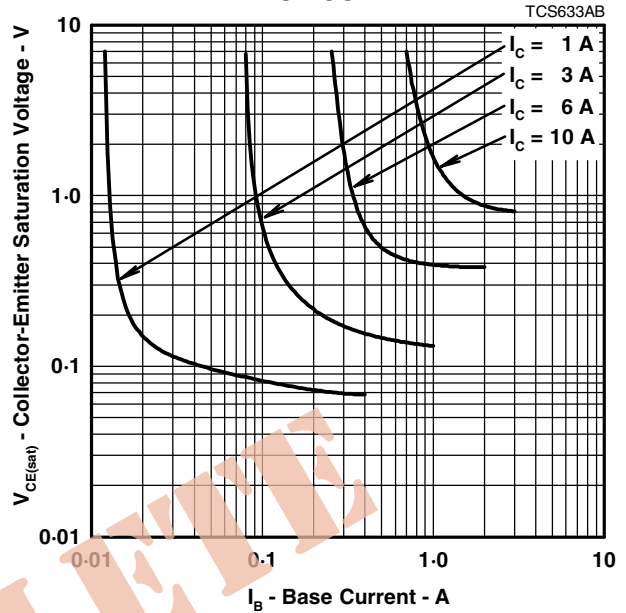


Figure 2.

**BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT**

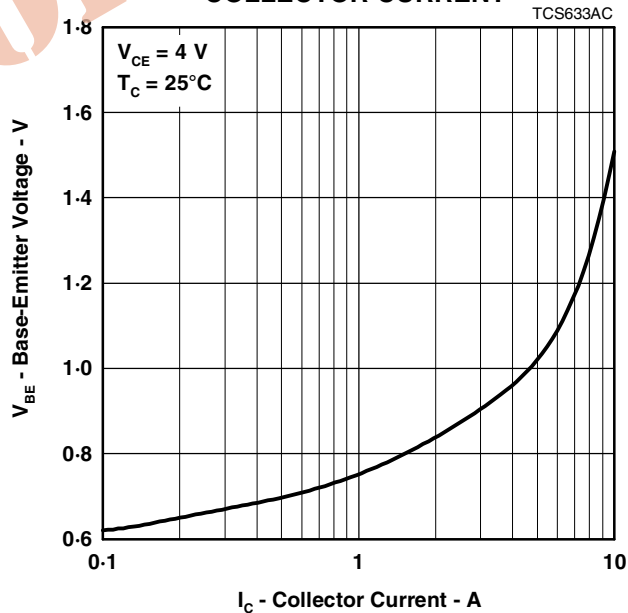


Figure 3.

PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

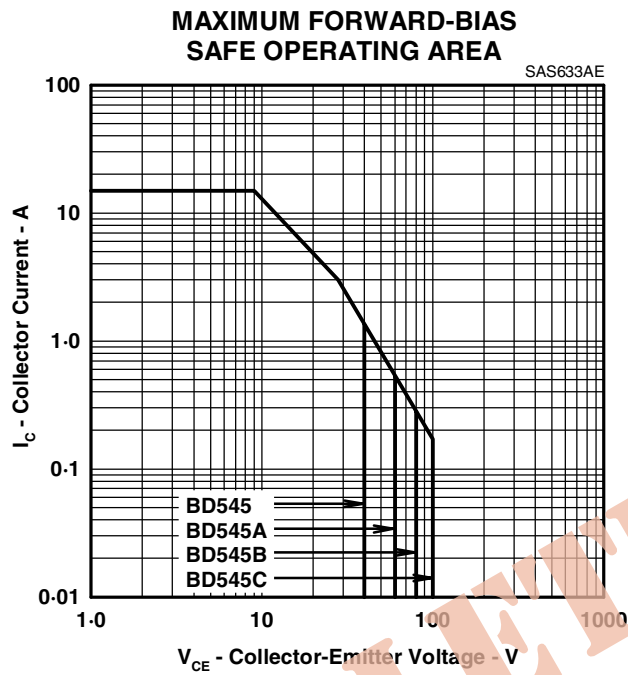


Figure 4.

THERMAL INFORMATION

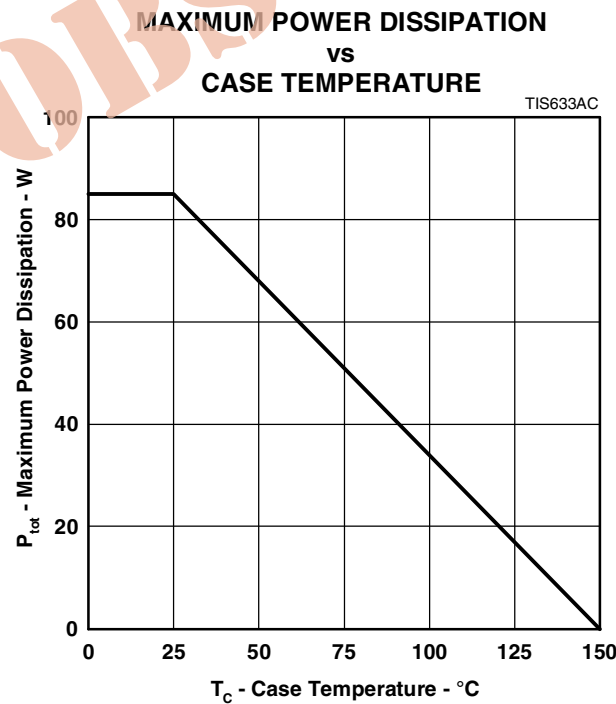


Figure 5.

PRODUCT INFORMATION